TECHNICAL DATA DATA SHEET 5035, REV. -

LOW RDS HERMETIC POWER MOSFET - P-CHANNEL

FEATURES:

- 60 Volt, 0.01 Ohm, 90A MOSFET
- Isolated Hermetic Metal Package
- Ultra Low R_{DS (on)}

MAXIMUM RATINGS

ALL RATINGS ARE AT $\rm T_{\rm C}$ = 25°C UNLESS OTHERWISE SPECIFIED.

RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	V_{GS}	-	-	±20	Volts
ON-STATE DRAIN CURRENT	I _{D25}	•	-	- 55*	Amps
PULSED DRAIN CURRENT	I _{DM}	ı	-	- 200	Amps
OPERATING AND STORAGE TEMPERATURE	T_{J}/T_{STG}	-55	-	+150	°C
TOTAL DEVICE DISSIPATION	P_{D}	•	-	205	Watts
THERMAL RESISTANCE, JUNCTION TO CASE	$R_{\theta JC}$	-	-	0.6	°C/W

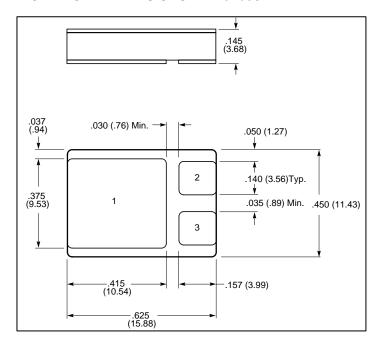
Note: * current limited by package; die rating is 90A

ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS
DRAIN TO SOURCE BREAKDOWN VOLTAGE	BV _{DSS}	- 60	-	-	Volts
$V_{GS} = 0V, I_{D} = -250\mu A$					
STATIC DRAIN TO SOURCE ON STATE RESISTANCE	R _{DS(ON)}				Ω
$V_{GS} = -10V, I_{D} = -30A$		-	0.008	0.010	
$V_{GS} = -4.5V, I_D = -20A$			0.010	0.012	
GATE THRESHOLD VOLTAGE $V_{DS} = V_{GS}$, $I_D = -250 \mu A$	$V_{GS(th)}$	- 1	-	- 3	Volts
FORWARD TRANSCONDUCTANCE	g fs	20	-	-	S(1/Ω)
$V_{DS} = -15V, I_{D} = -50A$					
ZERO GATE VOLTAGE DRAIN CURRENT					
$V_{DS} = 0.8 \text{ x Max. rating}, V_{GS} = 0V, T_J = 25^{\circ}C$	I _{DSS}	-	-	- 1	μΑ
$T_J = 125$ °C	_			- 50	_
GATE TO SOURCE LEAKAGE FORWARD V _{GS} = 20V	I_{GSS}	-	-	100	nA
GATE TO SOURCE LEAKAGE REVERSE V _{GS} = -20V	4		00	-100	
TURN ON DELAY TIME V _{DD} = -30V	t _{d(ON)}	-	20	-	2000
RISE TIME $I_D = -55A$	t _r		190		nsec
TURN OFF DELAY TIME V _{GS} = - 10V	t		140		
FALL TIME $R_G = 2.5\Omega$	$t_{d(OFF)}$		300		
DIODE FORWARD VOLTAGE $I_F = -55A$, $V_{GS} = 0V$	V _{SD}	_	- 1.0	- 1.5	Volts
Pulse test, $t \le 300 \mu s$, duty cycle $d \le 2 \%$	• 30		1.0	1.0	7 0.1.0
REVERSE RECOVERY TIME $T_{\perp} = 25^{\circ}C$.					
I_{F} = - 50A, V_{R} = - 30V	t _{rr}	_	60	90	nsec
di/dt = - 100A/μsec					
REVERSE RECOVERY CURRENT	Irr	-	- 3	- 4.5	Α
INPUT CAPACITANCE $V_{GS} = 0 V$,	C _{iss}	-	9200	-	
OUTPUT CAPACITANCE $V_{DS} = -25 \text{ V},$	Coss		975		pF
REVERSE TRANSFER CAPACITANCE f = 1.0MHz	C _{rss}		760		-

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MECHANICAL DIMENSIONS: in Inches / mm



LCC-3P

PINOUT TABLE

DEVICE TYPE	PIN 1	PIN 2	PIN 3
P CHANNEL MOSFET IN A LCC-3P PACKAGE	DRAIN	SOURCE	GATE
LCC-SP PACKAGE			

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